

UNISONIC TECHNOLOGIES CO., LTD

5N70K-MT Power MOSFET

5A, 700V N-CHANNEL **POWER MOSFET**

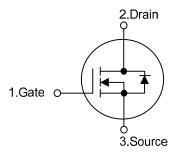
DESCRIPTION

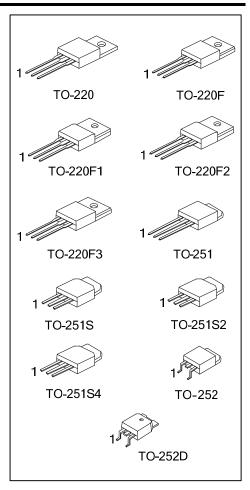
The UTC 5N70K-MT is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications at power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)}$ < 2.40 @ V_{GS} =10V, I_{D} = 2.5 A
- * Fast Switching Capability
- * Improved dv/dt Capability, High Ruggedness

SYMBOL





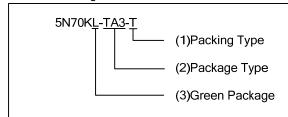
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5N70K-MT **Power MOSFET**

ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
5N70KL-TA3-T	5N70KG-TA3-T	TO-220	G	D	S	Tube	
5N70KL-TF3-T	5N70KG-TF3-T	TO-220F	G	D	S	Tube	
5N70KL-TF1-T	5N70KG-TF1-T	TO-220F1	G	D	S	Tube	
5N70KL-TF2-T	5N70KG-TF2-T	TO-220F2	G	D	S	Tube	
5N70KL-TF3-T	5N70KG-TF3-T	TO-220F3	G	D	S	Tube	
5N70KL-TM3-T	5N70KG-TM3-T	TO-251	G	D	S	Tube	
5N70KL-TMS-T	5N70KG-TMS-T	TO-251S	G	D	S	Tube	
5N70KL-TMS2-T	5N70KG-TMS2-T	TO-251S2	G	D	S	Tube	
5N70KL-TMS4-T	5N70KG-TMS4-T	TO-251S4	G	D	S	Tube	
5N70KL-TN3-R	5N70KG-TN3-R	TO-252	G	D	S	Tape Reel	
5N70KL-TND-R	5N70KG-TND-R	TO-252D	G	D	S	Tape Reel	

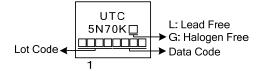
Note: Pin Assignment: G: Gate D: Drain S: Source



- (1) T: Tube, R: Tape Reel
- (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F3, TM3: TO-251 TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4, TN3: TO-252, TND: TO-252D

(3) L: Lead Free, G: Halogen Free and Lead Free

MARKING





■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	700	V	
Gate-Source Voltage		V_{GSS}	±30	V	
Avalanche Current (Note 2)		I _{AR}	5	Α	
Continuous Drain Current		I_{D}	5	Α	
Pulsed Drain Current (Note 2)		I_{DM}	20	Α	
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	150	m	
	Repetitive (Note 2)	E _{AR}	10	mJ	
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns	
	TO-220	P _D	108	W	
Power Dissipation	TO-220F/TO-220F1			36	W
	TO-220F3		36	VV	
	TO-220F2		38	W	
	TO-251/TO-251S		ı		
	TO-251S2/TO-251S4		54	W	
	TO-252/TO-252D				
Junction Temperature		T_J	+150	°C	
Operation Temperature		T_OPR	-55~+150	°C	
Storage Temperature		T_{STG}	-55~+150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Pulse width limited by $T_{J(MAX)}$
- 3. L=12mH, I_{AS}=5A, V_{DD}=50V, R_G=25 Ω , Starting T_J = 25°C
- 4. $I_{SD} \le 5A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$

■ THERMAL DATA

PARAMETER		SYMBOL RATINGS		UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3	0	62.5	°C/W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D	$ heta_{ m JA}$	110	°C/W
Junction to Case	TO-220		1.15	°C/W
	TO-220F/TO-220F1 TO-220F3		3.47	°C/W
	TO-220F2	θις	3.28	°C/W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		2.30	°C/W



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	700			V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} =700V, V _{GS} = 0V			1	μA		
Forward	,	V_{GS} =30V, V_{DS} = 0V			100	Λ		
Gate-Source Leakage Current Reverse	- I _{GSS}	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA		
Breakdown Voltage Temperature Coefficient	nt ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.6		V/°C		
ON CHARACTERISTICS	ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V		
Static Drain-Source On-State Resistance	R _{DS(ON)}	$V_{GS} = 10V, I_D = 2.5A$		1.86	2.4	Ω		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{ISS}	V 05V V 0V		515	670	pF		
Output Capacitance	Coss	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz		55	72	pF		
Reverse Transfer Capacitance	C _{RSS}	71 = 1.0WH2		6.5	8.5	pF		
SWITCHING CHARACTERISTICS								
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 30V, I _D =0.5A,		50		ns		
Turn-On Rise Time	t _R			40		ns		
Turn-Off Delay Time	t _{D(OFF)}	$R_G = 25\Omega \text{ (Note 1, 2)}$		180		ns		
Turn-Off Fall Time	t _F			52		ns		
Total Gate Charge	Q_G	$V_{DS} = 50 \text{ V}, I_{D} = 1.3\text{A},$		18	23	nC		
Gate-Source Charge	Q_{GS}	$V_{GS} = 50 \text{ V}, I_D = 1.3\text{A},$ $V_{GS} = 10 \text{ V} \text{ (Note 1, 2)}$		6.7		nC		
Gate-Drain Charge	Q_GD	VGS - 10 V (NOIE 1, 2)		3.9		nC		
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS								
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 5A$			1.4	V		
Maximum Continuous Drain-Source Diode					5			
Forward Current	I _S				5	Α		
Maximum Pulsed Drain-Source Diode	lau				20	Α		
Forward Current	I _{SM}				20	^		

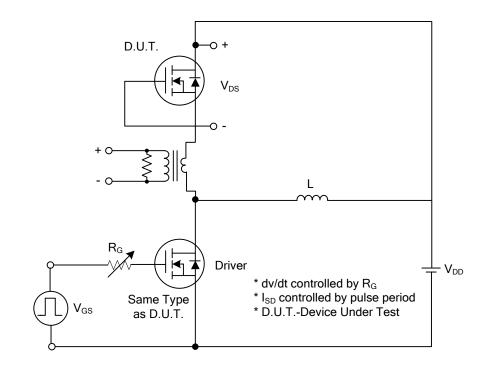
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature

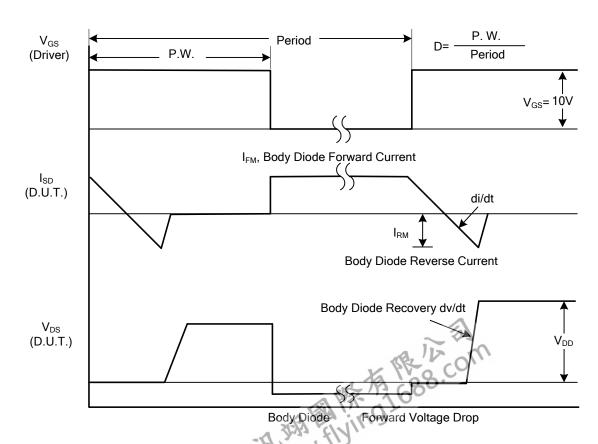


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■ TEST CIRCUITS AND WAVEFORMS



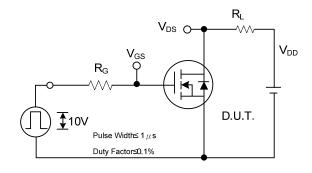
Peak Diode Recovery dv/dt Test Circuit

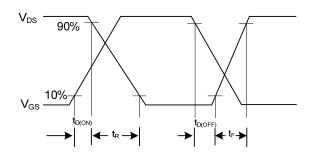


Peak Diode Recovery dv/dt Waveforms

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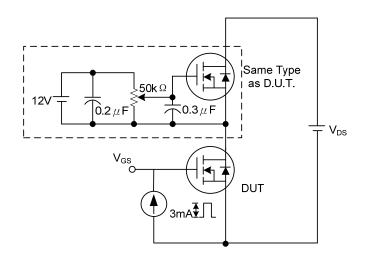
TEST CIRCUITS AND WAVEFORMS (Cont.)

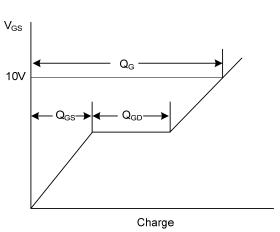




Switching Test Circuit

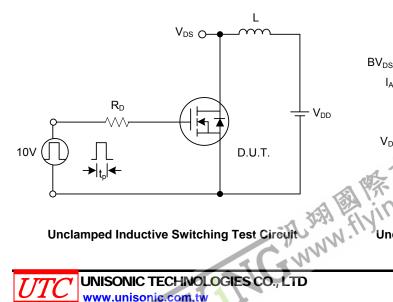
Switching Waveforms

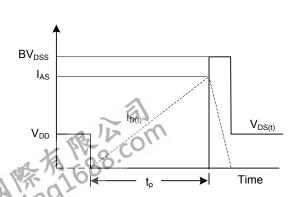




Gate Charge Test Circuit

Gate Charge Waveform





Unclamped Inductive Switching Waveforms

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